

NTMFS4C05N

- Surface-mounted on FR4 board using the minimum recommended pad size.
- This is the absolute maximum ratings. Parts are 100% tested at $T_J = 25^\circ\text{C}$, $V_{GS} = 20\text{ V}$, $I_L = 29\text{ A}$, $E_{AS} = 42\text{ mJ}$.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	3.8	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	48.6	
Junction-to-Ambient – Steady State (Note 5)	$R_{\theta JA}$	161.7	
Junction-to-Ambient – ($t \leq 10\text{ s}$) (Note 4)	$R_{\theta JA}$	19	

- Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$, $I_D = 250\ \mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage (transient)	$V_{(BR)DSS(t)}$	$V_{GS} = 0\text{ V}$, $I_{D(aval)} = 12.6\text{ A}$, $T_{case} = 25^\circ\text{C}$, $t_{transient} = 100\text{ ns}$	34			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			12		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$, $V_{DS} = 24\text{ V}$			1.0	μA
		$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 6)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	1.3		2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			5.1		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 30\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 30\text{ A}$		2.7	3.4	$\text{m}\Omega$
				4.0	5.0	
Forward Transconductance	g_{FS}	$V_{DS} = 1.5\text{ V}$, $I_D = 15\text{ A}$		68		S
Gate Resistance	R_G	$T_A = 25^\circ\text{C}$	0.3	1.0	2.0	Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$, $V_{DS} = 15\text{ V}$		1972		pF
Output Capacitance	C_{OSS}			1215		
Reverse Transfer Capacitance	C_{RSS}			59		
Capacitance Ratio	C_{RSS}/C_{ISS}	$V_{GS} = 0\text{ V}$, $V_{DS} = 15\text{ V}$, $f = 1\text{ MHz}$		0.030		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 30\text{ A}$		14		nC
Threshold Gate Charge	$Q_{G(TH)}$			3.3		
Gate-to-Source Charge	Q_{GS}			6.0		
Gate-to-Drain Charge	Q_{GD}			5.0		
Gate Plateau Voltage	V_{GP}			3.1		
Total Gate Charge	$Q_{G(TOT)}$		$V_{GS} = 10\text{ V}$, $V_{DS} = 15\text{ V}$; $I_D = 30\text{ A}$		30	

SWITCHING CHARACTERISTICS (Note 7)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}$, $V_{DS} = 15\text{ V}$, $I_D = 15\text{ A}$, $R_G = 3.0\ \Omega$		11		ns
Rise Time	t_r			32		
Turn-Off Delay Time	$t_{d(OFF)}$			21		
Fall Time	t_f			7.0		

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 7)						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 15\text{ A}, R_G = 3.0\ \Omega$		8.0		ns
Rise Time	t_r			26		
Turn-Off Delay Time	$t_{d(OFF)}$			26		
Fall Time	t_f			5.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 10\text{ A}$	$T_J = 25^\circ\text{C}$		0.77	1.1	V
			$T_J = 125^\circ\text{C}$		0.62		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$			40.2		ns
Charge Time	t_a				20.3		
Discharge Time	t_b				19.9		
Reverse Recovery Charge	Q_{RR}					30.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

7. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

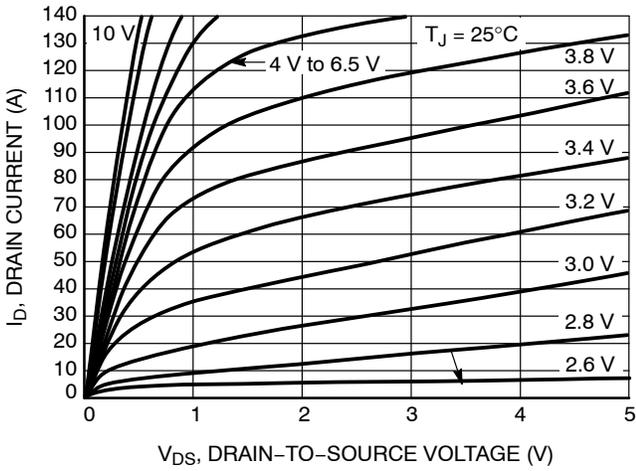


Figure 1. On-Region Characteristics

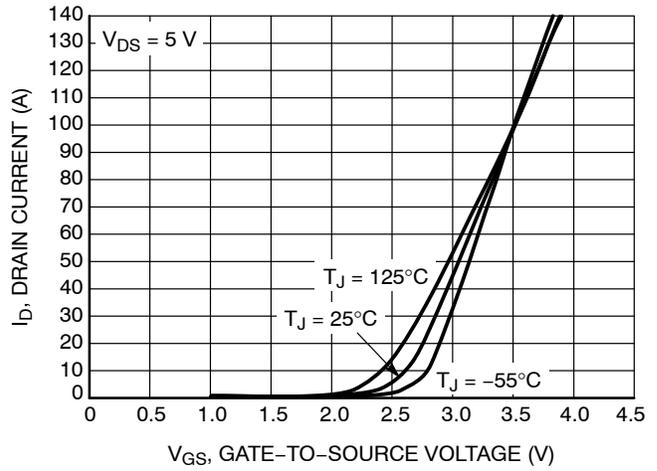


Figure 2. Transfer Characteristics

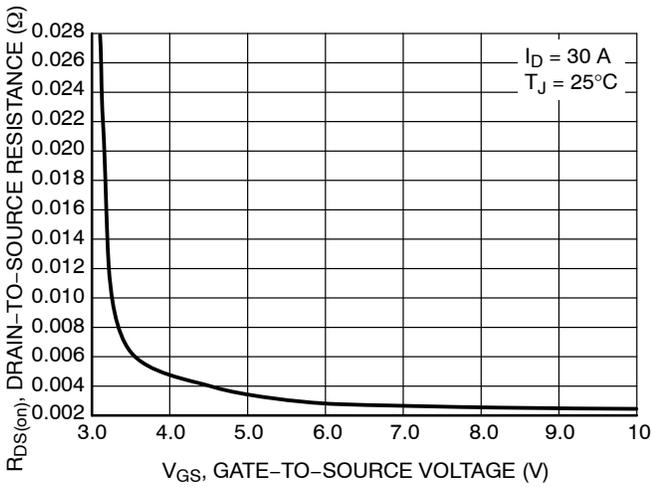


Figure 3. On-Resistance vs. V_{GS}

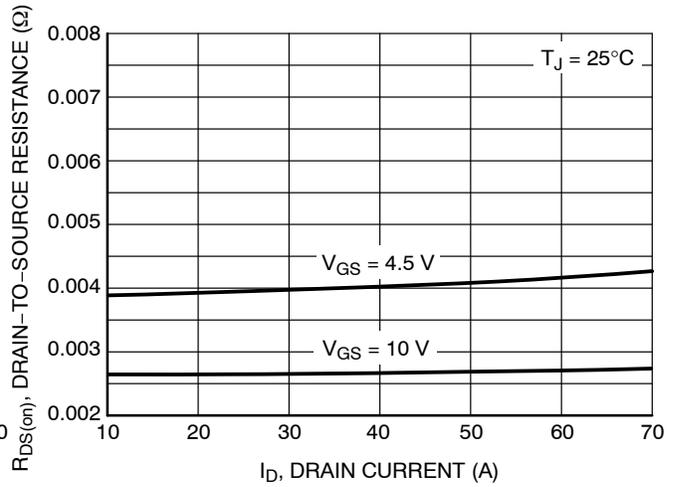


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

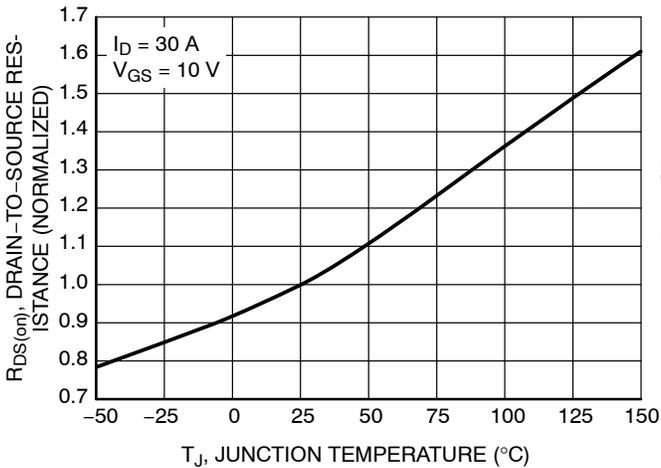


Figure 5. On-Resistance Variation with Temperature

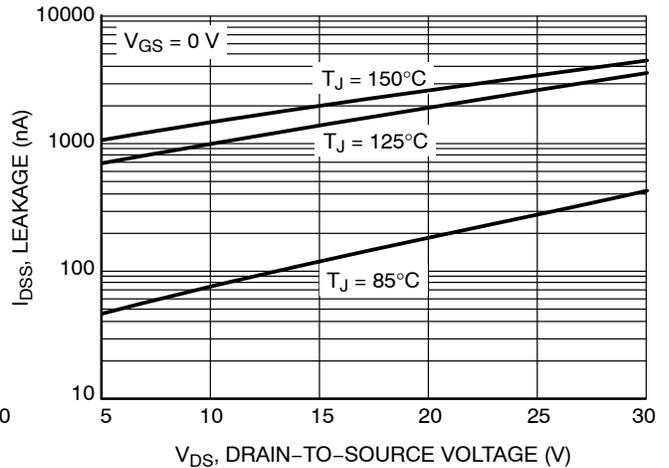


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

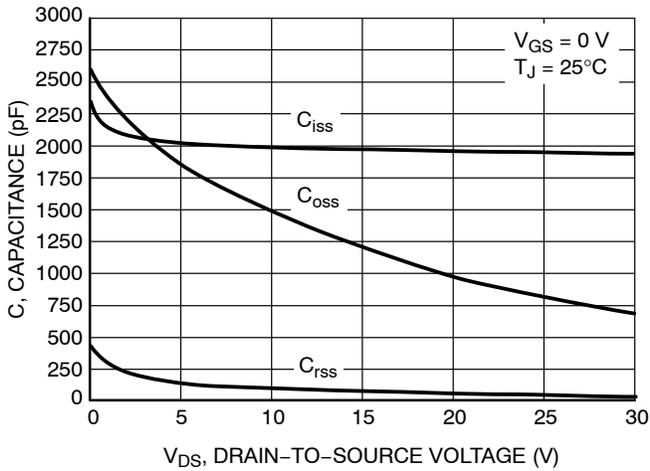


Figure 7. Capacitance Variation

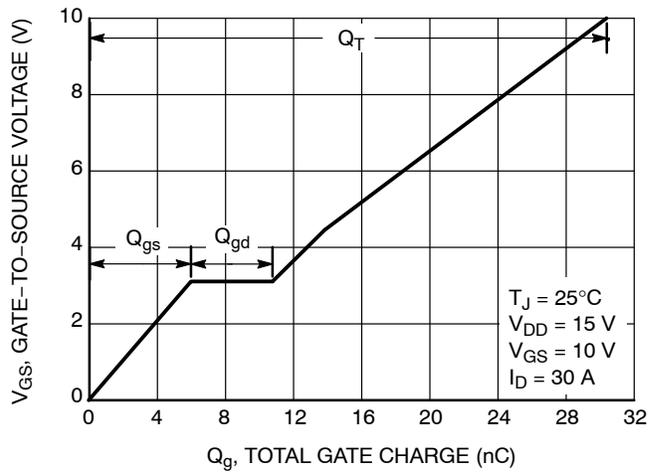


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

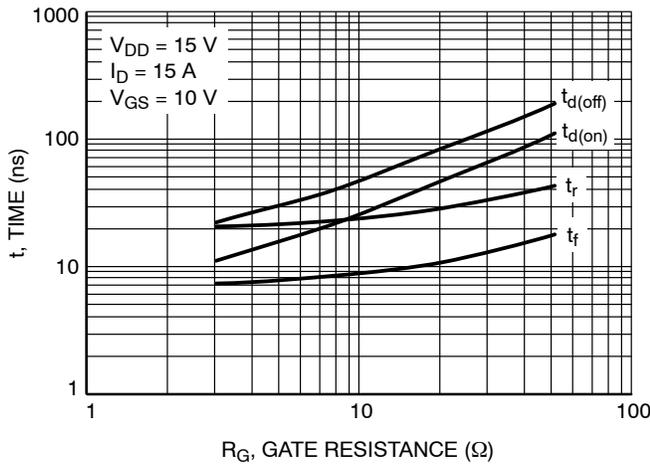


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

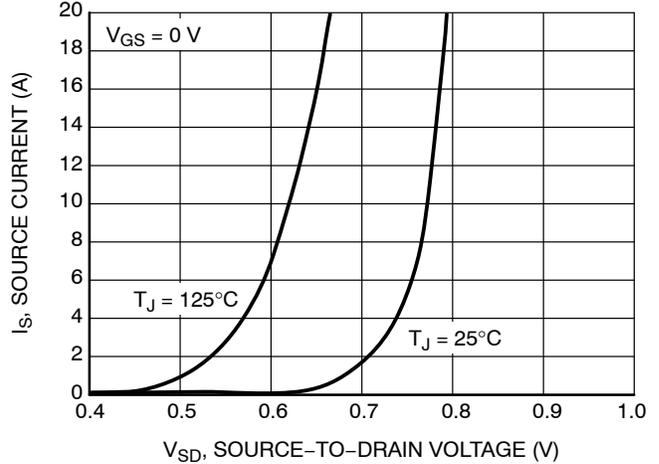


Figure 10. Diode Forward Voltage vs. Current

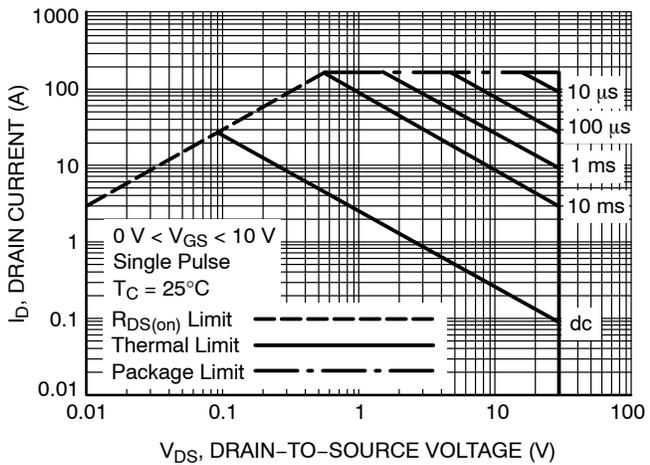


Figure 11. Maximum Rated Forward Biased Safe Operating Area

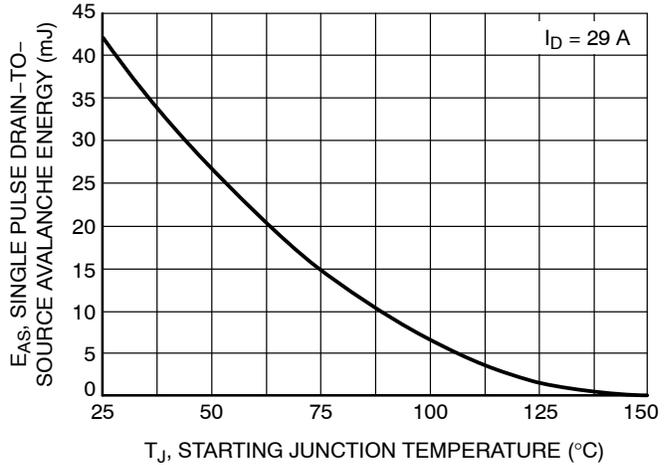


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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TYPICAL CHARACTERISTICS

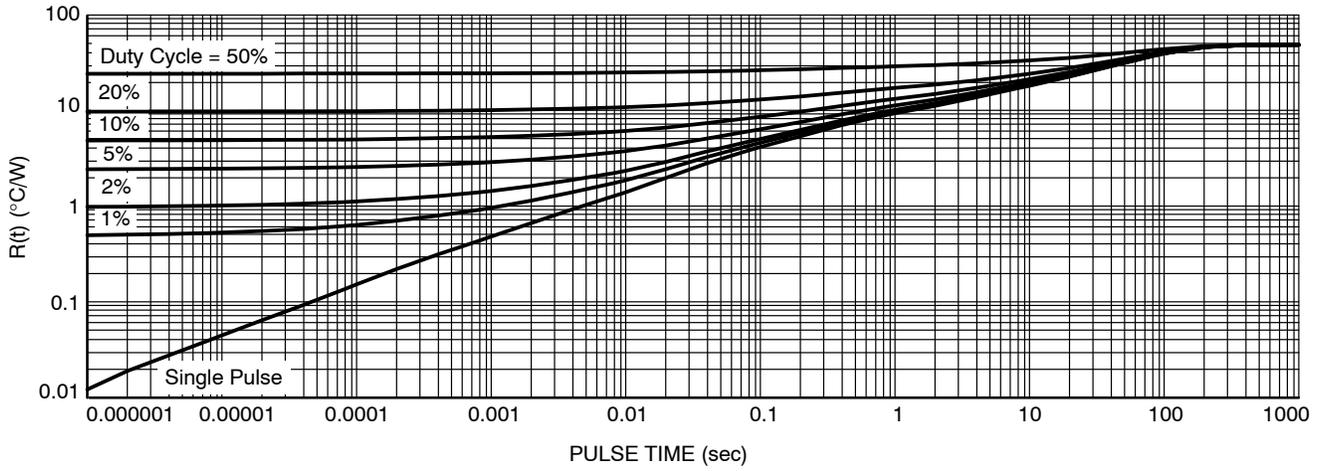


Figure 13. Thermal Response

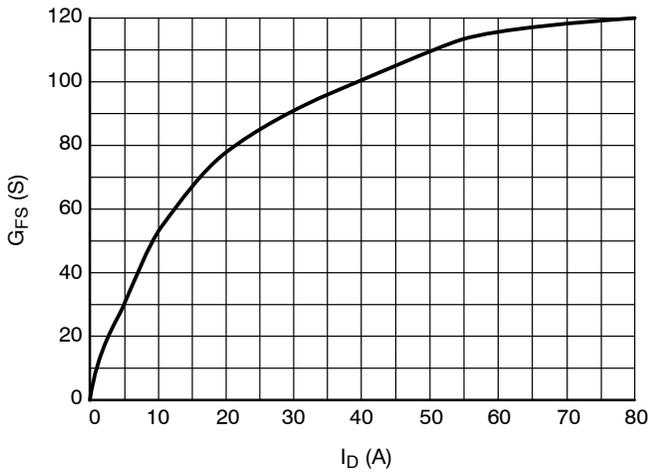


Figure 14. G_{FS} vs. I_D

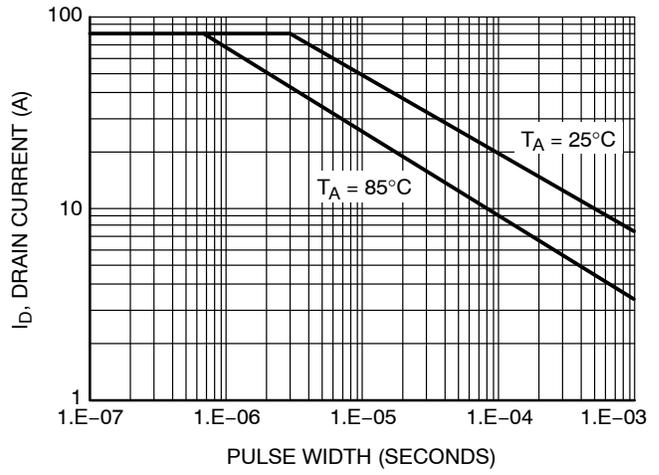


Figure 15. Avalanche Characteristics

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

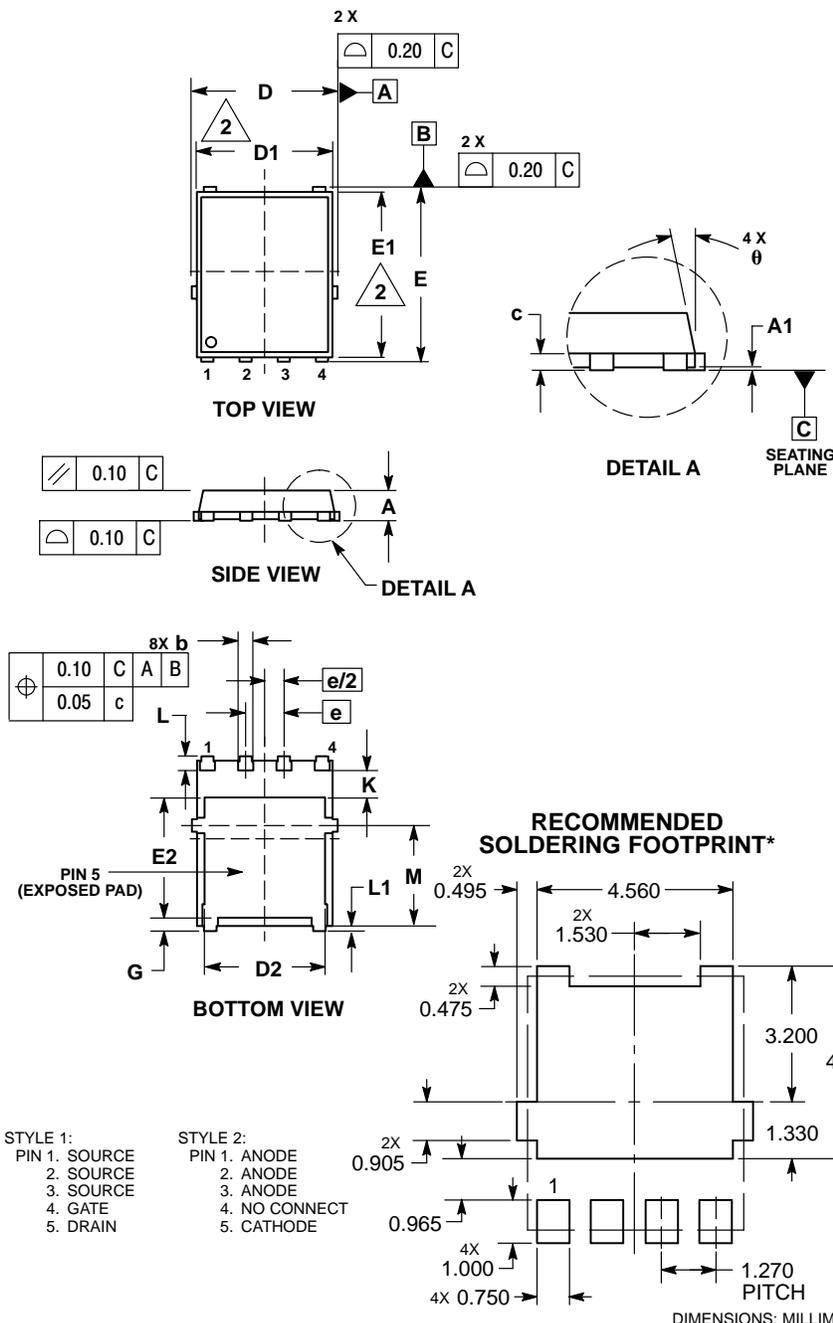
ON Semiconductor®



1
SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

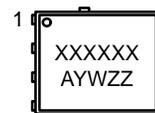
DATE 25 JUN 2018



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0°	---	12°

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

- STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
- STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)	PAGE 1 OF 1

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